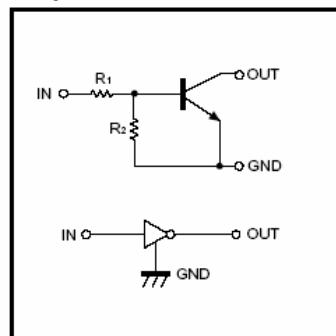


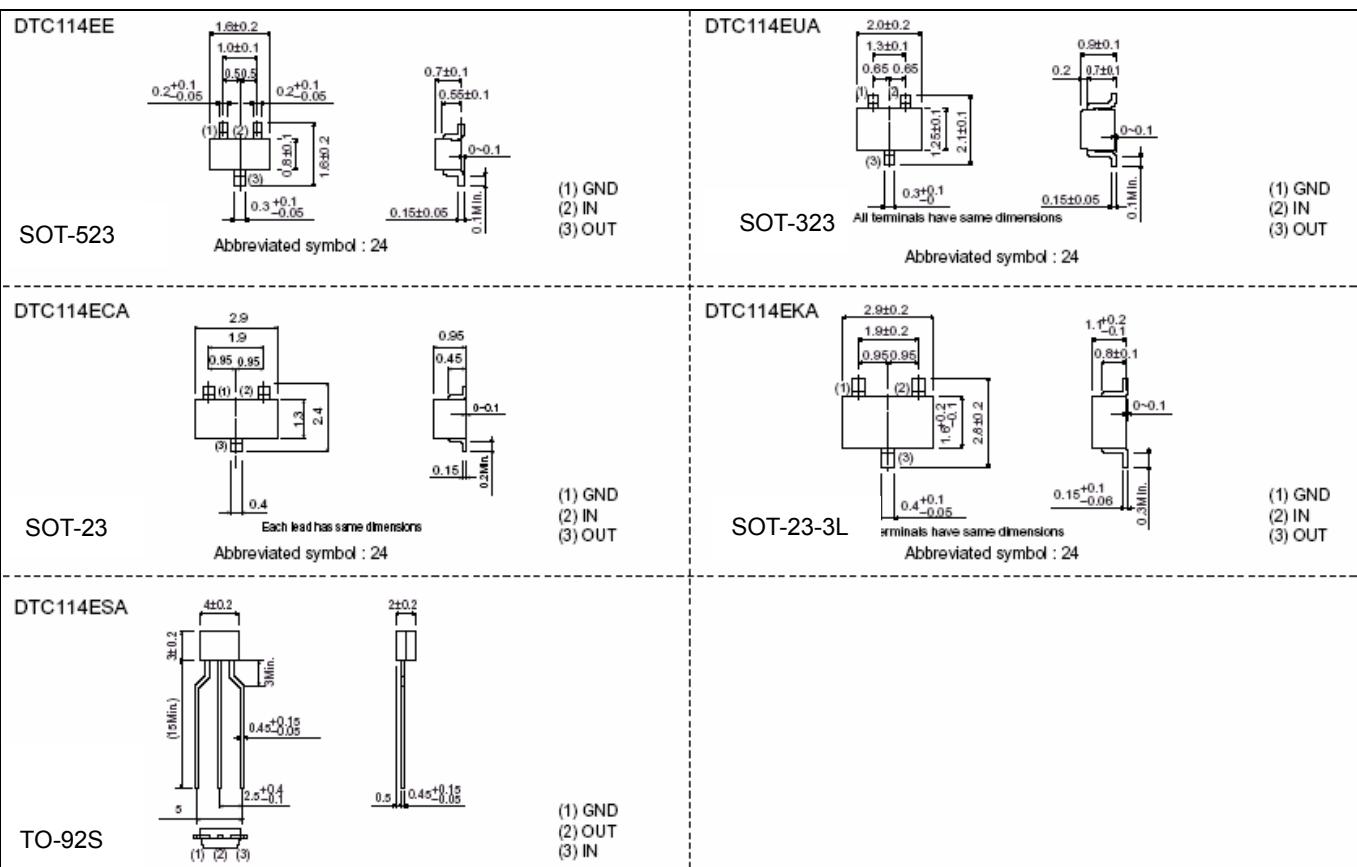
FEATURES

- * Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- * Only the on/off conditions need to be set for operation making device design easy.
- * The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.

● Equivalent circuit



External dimensions (Units:mm)



Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	Limits (DTC114E□)					Unit
		E	UA	CA	KA	SA	
Supply voltage	V _{CC}			50			V
Input voltage	V _{IN}			-10~40			V
Output current	I _O			50			mA
	I _{C(MAX)}			100			
Power dissipation	P _d	150		200		300	mW
Junction temperature	T _j			150			°C
Storage temperature	T _{stg}			-55~150			°C

Electrical characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Input voltage	$V_{I(\text{off})}$			0.5	V	$V_{CC}=5\text{V}, I_O=100\mu\text{A}$
	$V_{I(\text{on})}$	3				$V_O=0.3\text{V}, I_O=10 \text{ mA}$
Output voltage	$V_{O(\text{on})}$			0.3	V	$I_O/I_I=10\text{mA}/0.5\text{mA}$
Input current	I_I			0.88	mA	$V_I=5\text{V}$
Output current	$I_O(\text{off})$			0.5	μA	$V_{CC}=50\text{V}, V_I=0$
DC current gain	G_I	30				$V_O=5\text{V}, I_O=5\text{mA}$
Input resistance	R_I	7	10	13	$\text{k}\Omega$	
Resistance ratio	R_2/R_1	0.8	1	1.2		
Transition frequency	f_T		250		MHz	$V_{CE}=10\text{V}, I_E=-5\text{mA}, f=100\text{MHz}$

Typical Characteristics

● Electrical characteristic curves

